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(54) **SEMICONDUCTOR LIGHT EMITTING
DEVICE AND A DISPLAY DEVICE**

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(57) **ABSTRACT**

Discussed is a semiconductor light emitting device can include a light emitting layer, a passivation layer on an upper surface and a side surface of the light emitting layer, a protective layer on a lower surface and the side surface of the light emitting layer, a first electrode between the light emitting layer and the protective layer, and a second electrode between the light emitting layer and the passivation layer. An inner angle between the side surface and the lower surface of the light emitting layer can have an obtuse angle.

